

$V_{DS}$	1200 V
$R_{DS,on}$	10 m $\Omega$
$I_D (T_C=25^\circ C)$	202 A
$T_{J,max}$	175 $^\circ C$

## 1200V SiC MOSFET Power Module

### Features

- High speed switching SiC MOSFETs
- Simple to drive
- Kelvin reference for stable operation

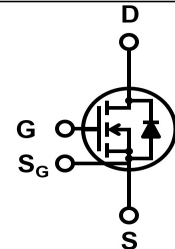
### Benefits

- Low switching losses
- Low junction to case thermal resistance
- Very rugged and easy mount
- Direct mounting to heatsink (isolated package)

### Applications

- Photovoltaic Inverter
- Battery charger
- Server power supplies
- Energy storage system

### Package



- (1)  $S_G$  (Driver Source)
- (2) G (Gate)
- (3) D (Drain)
- (4) S (Source)

Part #	Package	Marking
GCMX010B120S1-E1	SOT-227	GCMX010B120S1-E1

PRELIMINARY



### Absolute Maximum Ratings

Characteristics	Symbol	Conditions	Values	Unit
Drain-Source Voltage	$V_{rated}$	$V_{GS}=0V, I_D=1\mu A$	1200	V
Continuous Drain Current	$I_{DS}$	$T_C=25^\circ C, V_{GS}=20V$	202	A
		$T_C=100^\circ C, V_{GS}=20V$	146	
Body Diode Drain Current	$I_{SD}$	$T_C=25^\circ C, V_{GS}=-5V$	161	
Pulsed Drain Current	$I_{DS,pulse}^*$	$T_C=25^\circ C, V_{GS}=20V$	500	
Gate Source Voltage	$V_{GSmax}$		-10/25	V
	$V_{GSop}$	Recommended operational	-5/20	
Power Dissipation	$P_{tot}$	$T_C=25^\circ C$	750	W
Operating & Storage Temperature	$T_J, T_{storage}$	Continuous	-55...175	$^\circ C$

\*Pulse width is limited by  $T_{J,max}$

# 1200V SiC MOSFET Power Module

# GCMX010B120S1-E1

Static Electrical Characteristics, at  $T_J=25^\circ\text{C}$ , unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=1mA$	1200	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=1200V, V_{GS}=0V$	-	0.1	1	$\mu A$
		$V_{DS}=1200V, V_{GS}=0V, T_J=175^\circ\text{C}$	-	1	-	
Gate-Source Leakage Current	$I_{GSS+}$	$V_{GS}=20V, V_{DS}=0V$	-	<+10	100	nA
	$I_{GSS-}$	$V_{GS}=-5V, V_{DS}=0V$	-	>-10	-100	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=40mA$	1.8	3.3	4	V
		$V_{GS}=V_{DS}, I_D=40mA, T_J=175^\circ\text{C}$	-	2.3	-	
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=20V, I_D=100A$	-	10	14	m $\Omega$
		$V_{GS}=20V, I_D=50A$	-	9.3	45	
		$V_{GS}=20V, I_D=100A, T_J=125^\circ\text{C}$	-	13	-	
		$V_{GS}=20V, I_D=100A, T_J=175^\circ\text{C}$	-	16	-	
Transconductance	$g_{fs}$	$V_{DS}=20V, I_D=100A$	-	51	-	S
Internal Gate Resistance	$R_{G(int)}$	f=1MHz, $V_{AC}=25mV$ , D-S Short	-	0.4	-	$\Omega$

AC Electrical Characteristics, at  $T_J=25^\circ\text{C}$ , unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Input Capacitance	$C_{ISS}$	$V_{GS}=0V$	-	13567	-	pF
Output Capacitance	$C_{OSS}$	$V_{DS}=1000V$	-	539	-	
Reverse Transfer Capacitance	$C_{RSS}$	f=200kHz	-	29	-	
Coss Stored Energy	$E_{OSS}^*$	$V_{AC}=25mV$	-	310	-	$\mu J$
Turn-On Switching Energy	$E_{ON}$		-	2.26	-	mJ
Turn-Off Switching Energy	$E_{OFF}$	$V_{DD}=800V, I_{DS}=100A,$ $R_{G(ext)}=3.9\Omega,$	-	0.77	-	
Turn-On Delay Time	$t_{D(on)}$	$V_{GS}=-5/+20V, L=90\mu H,$	-	36	-	ns
Rise Time	$t_R$	FWD= GCMX010B120S1-E1	-	16	-	
Turn-Off Delay Time	$t_{D(off)}$		-	69	-	
Fall Time	$t_F$		-	27	-	
Total Gate Charge	$Q_G$	$V_{DD}=800V, I_{DS}=100A$	-	476	-	nC
Gate to Source Charge	$Q_{GS}$	$V_{GS}=-5/20V$	-	176	-	
Gate to Drain Charge	$Q_{GD}$		-	74	-	

\* $E_{OSS}$  is calculated from  $C_{OSS}$  curve

Body Diode Characteristics, at  $T_J=25^\circ\text{C}$ , unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Diode Forward Voltage	$V_{SD}$	$V_{GS}=-5V, I_S=50A$	-	4.1	-	V
Reverse Recovery Time	$t_{RR}$	$I_S=100A, V_R=800V, V_{GS}=-5V$	-	20	-	ns
Reverse Recovery Charge	$Q_{RR}$	di/dt=7.8A/ns	-	1203	-	nC
Peak Reverse Recovery Current	$I_{RRM}$		-	90	-	A

Thermal and Package Characteristics, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction-case	$R_{thJC}$		-	0.16	0.20	$^\circ\text{C/W}$
Mounting torque	$M_d$	M4-0.7 screws	1.1	-	1.5	N-m
Terminal connection torque	$M_{dt}$	M4-0.7 screws	-	1.1	1.3	
Package weight	$W_t$		-	32	-	g
Isolation voltage	$V_{ISOL}$	$I_{ISOL} < 1\text{mA}$ , 50/60 Hz, 2 s	4000	-	-	V

## Typical Performance

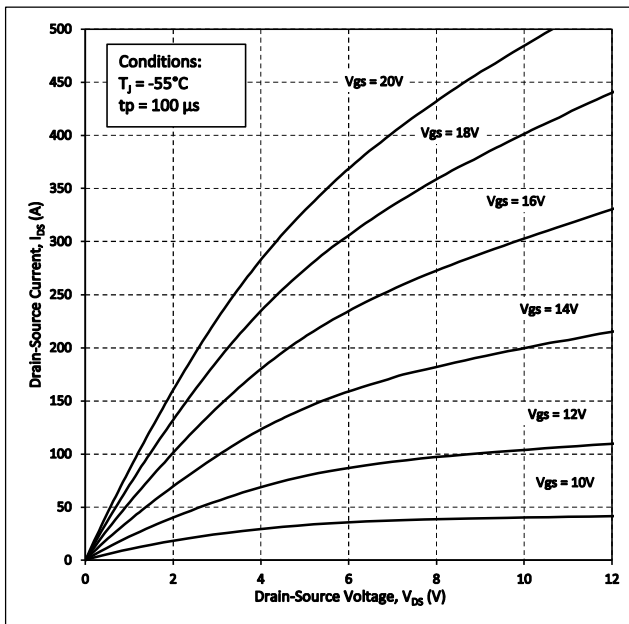


Figure 1. Output Characteristics  $T_j = -55^\circ\text{C}$

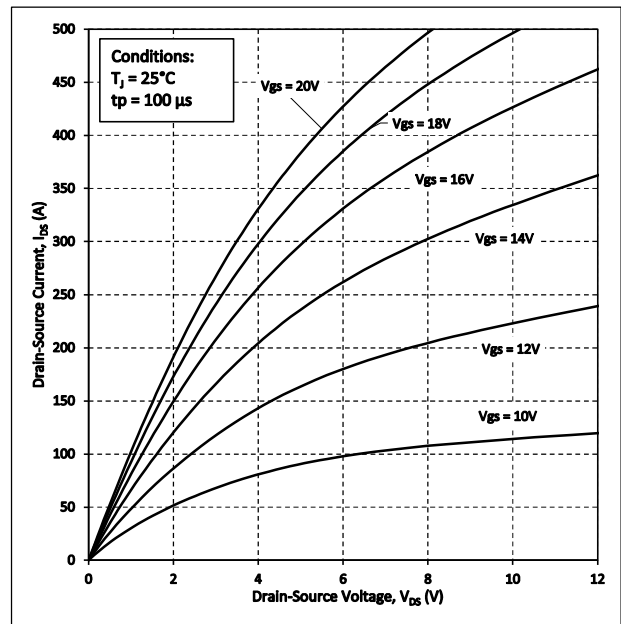


Figure 2. Output Characteristics  $T_j = 25^\circ\text{C}$

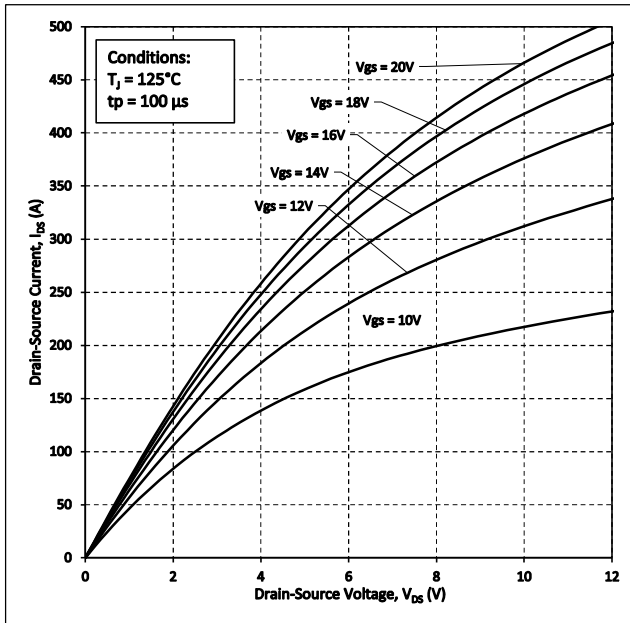


Figure 3. Output Characteristics  $T_J = 125^\circ\text{C}$

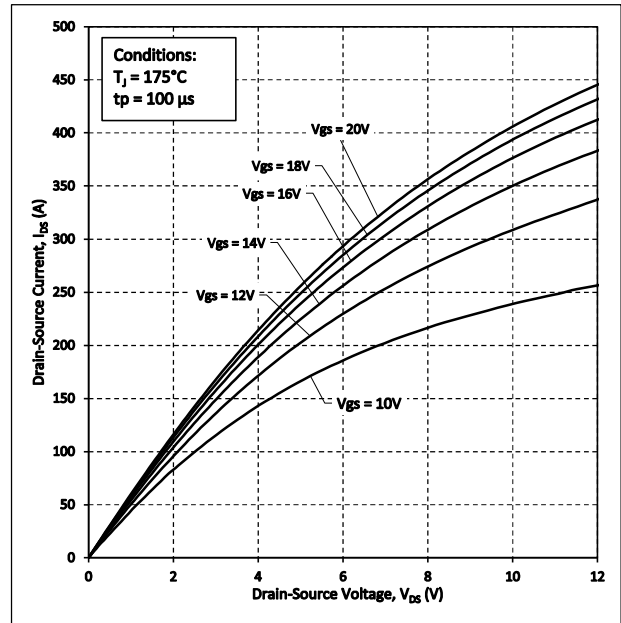


Figure 4. Output Characteristics  $T_J = 175^\circ\text{C}$

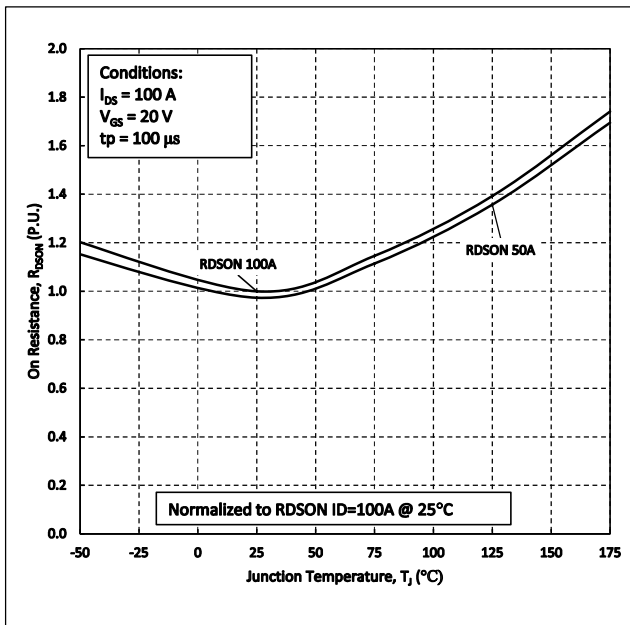


Figure 5. Normalized On-Resistance vs. Temperature

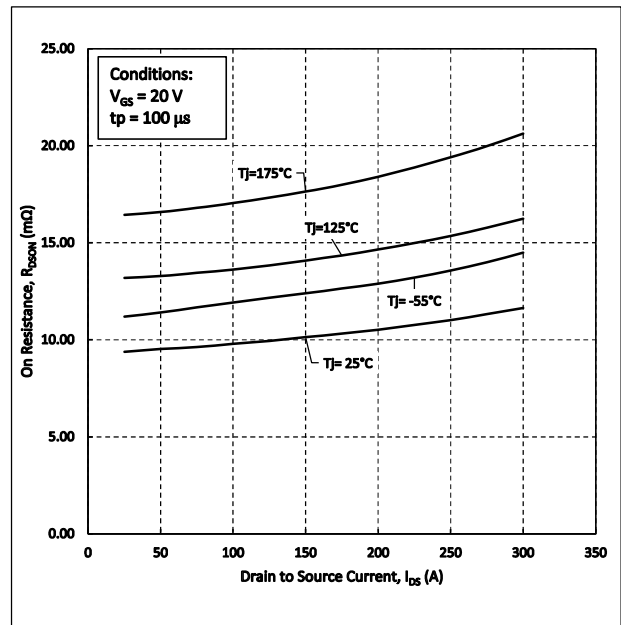


Figure 6. On-Resistance vs. Drain Current For Various Temperature

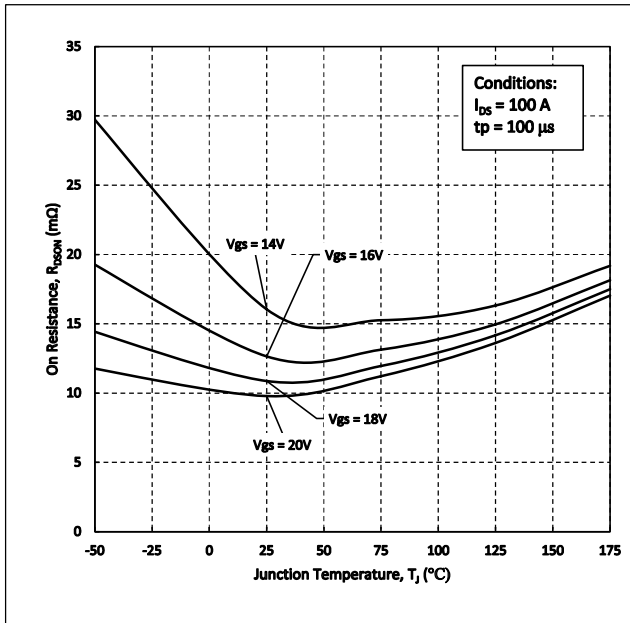


Figure 7. On-Resistance vs. Temperature For Various Gate Voltages

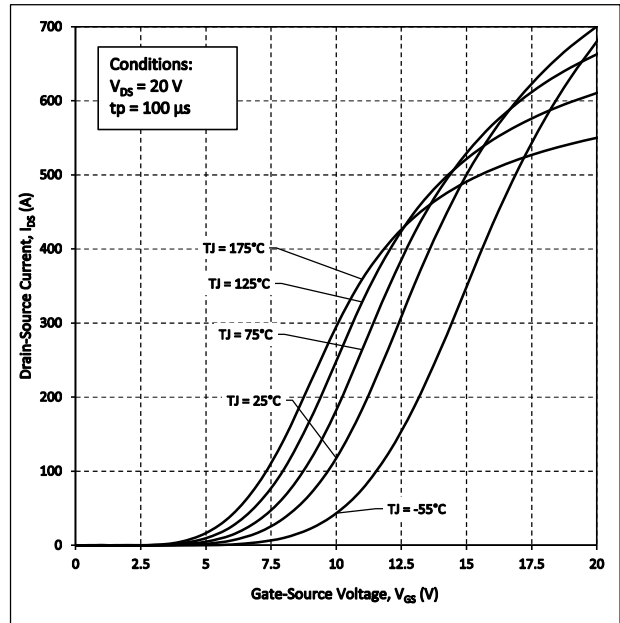


Figure 8. Transfer Characteristic for Various Junction Temperatures

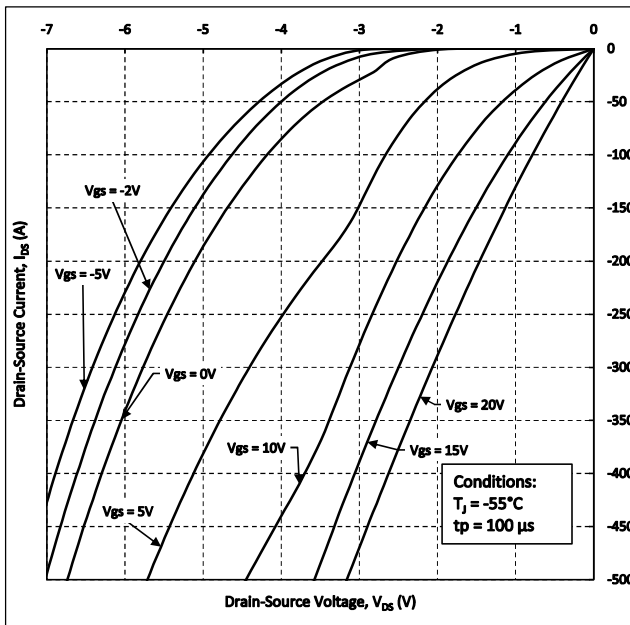


Figure 9. Body Diode Characteristics at  $T_J = -55^\circ\text{C}$

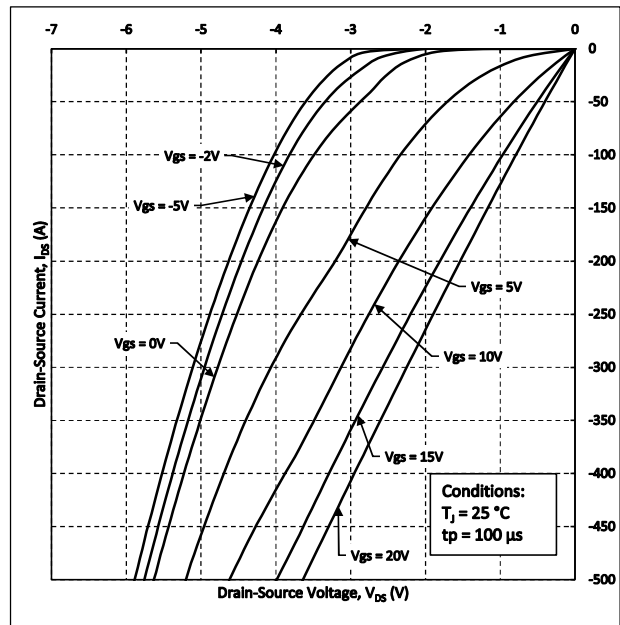


Figure 10. Body Diode Characteristics at  $T_J = 25^\circ\text{C}$

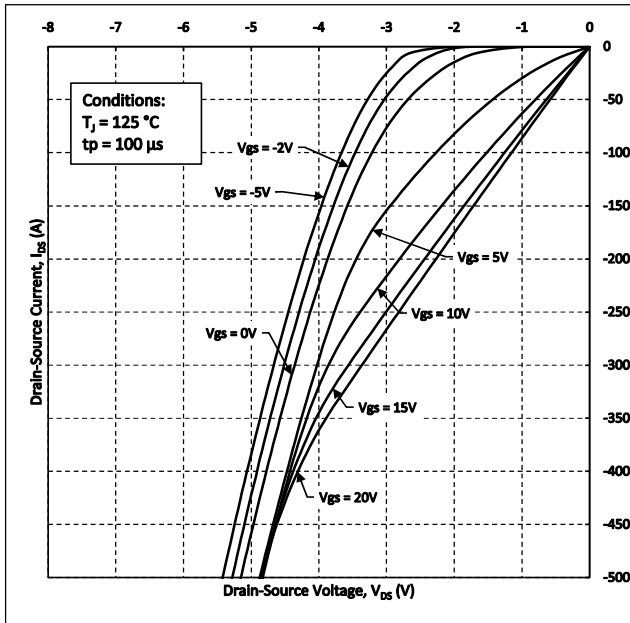


Figure 11. Body Diode Characteristics at  $T_J = 125^\circ\text{C}$

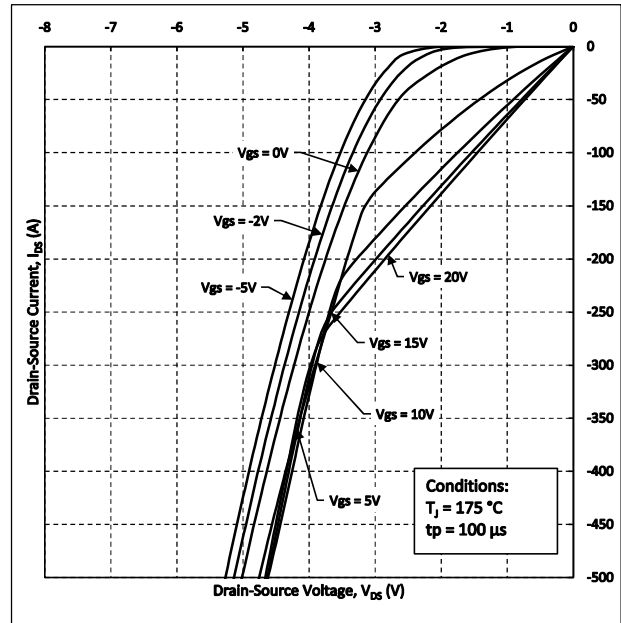


Figure 12. Body Diode Characteristics at  $T_J = 175^\circ\text{C}$

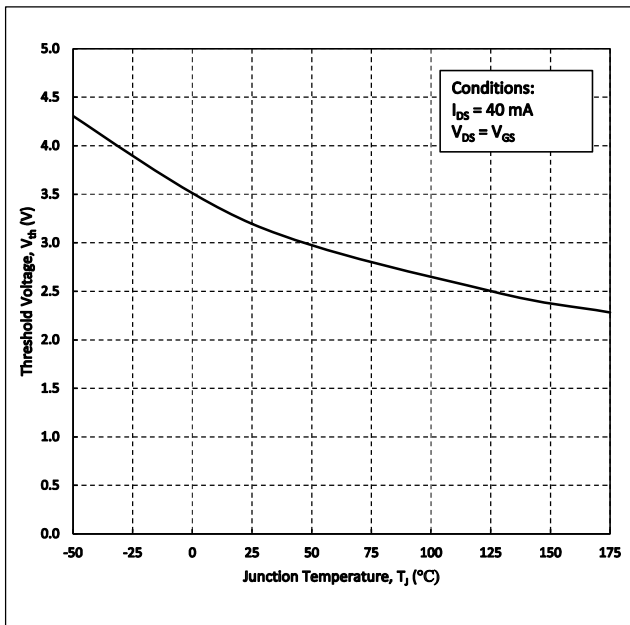


Figure 13. Threshold Voltage vs. Temperature

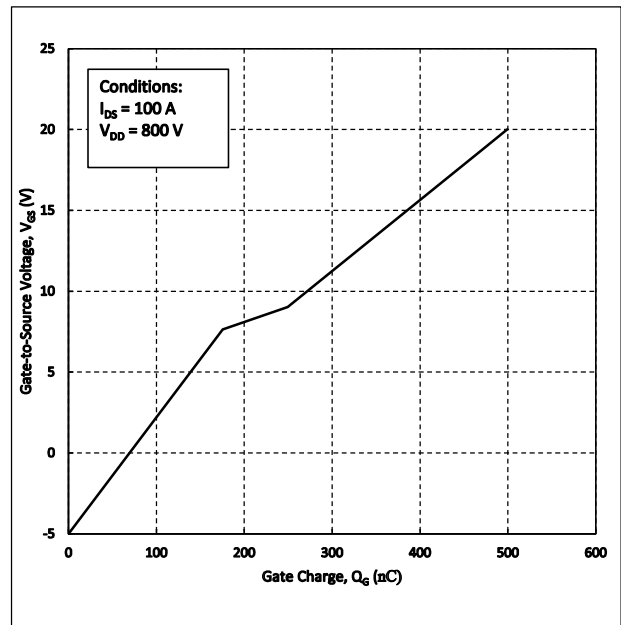


Figure 14. Gate Charge Characteristics

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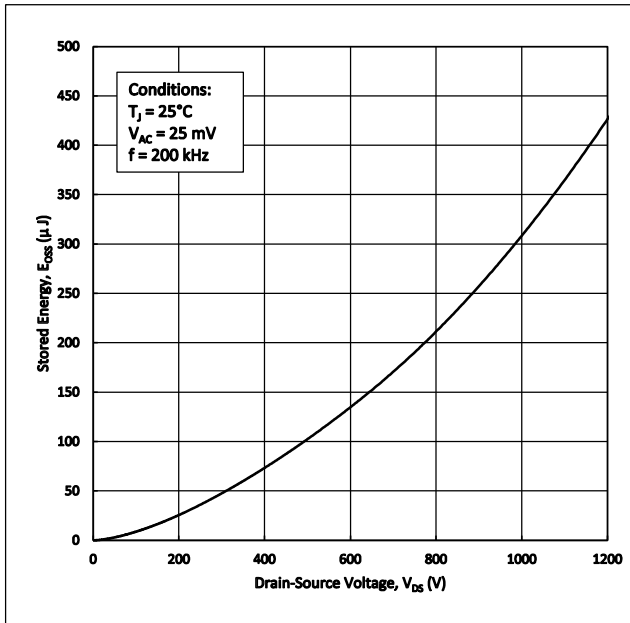


Figure 15. Output Capacitor Stored Energy

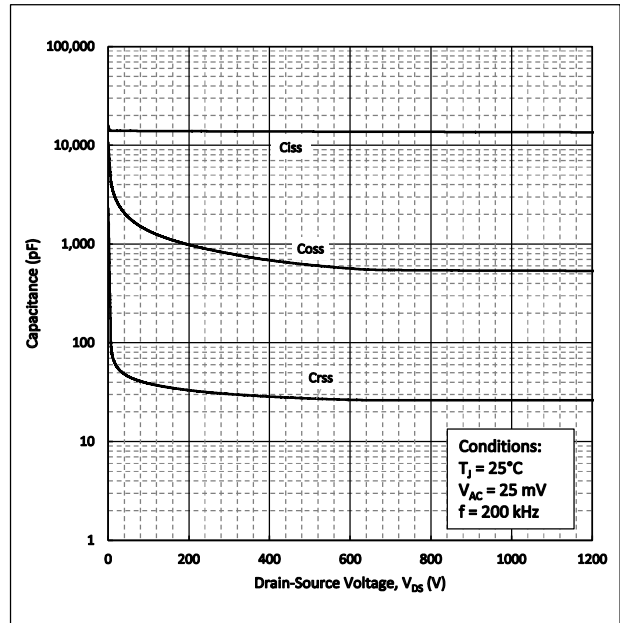


Figure 16. Capacitance vs Drain-Source Voltage

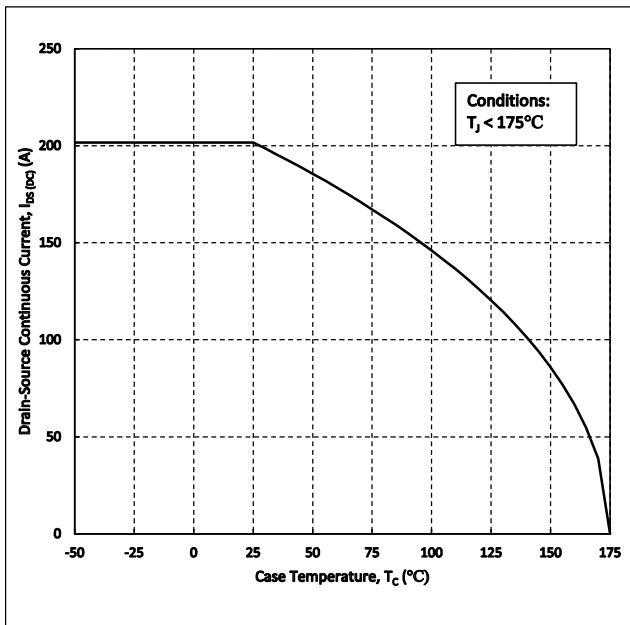


Figure 17. Continuous Drain Current Derating vs. Case Temperature

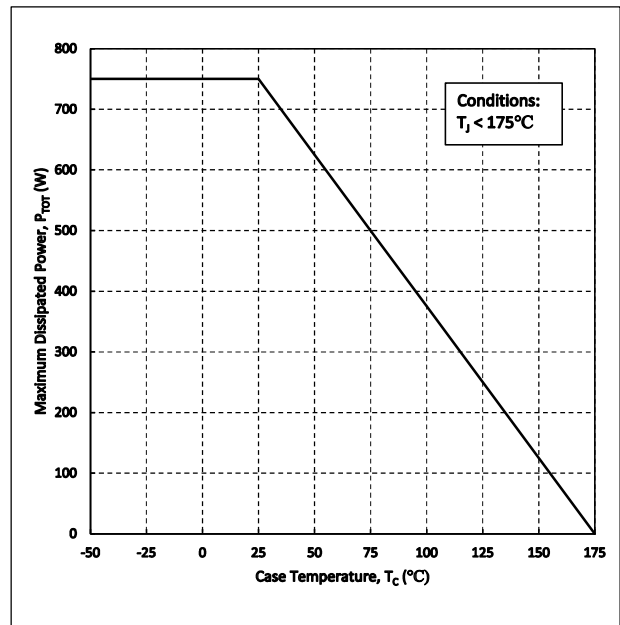


Figure 18. Maximum Power Dissipation Derating vs. Case Temperature

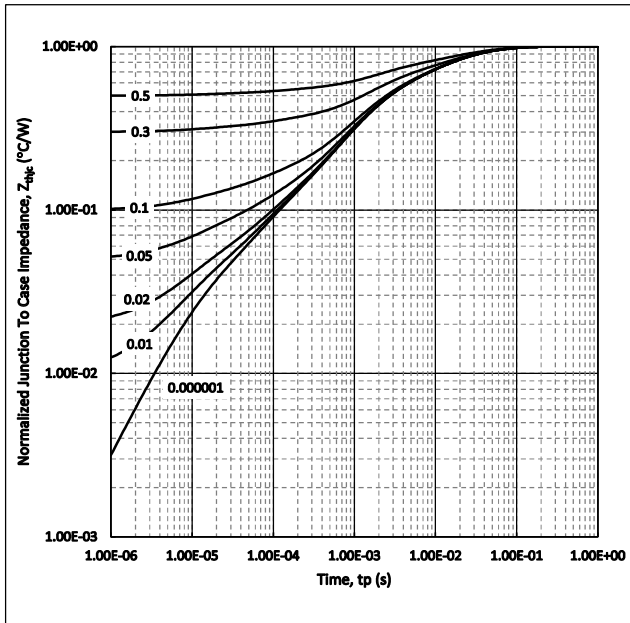


Figure 19. Transient Thermal impedance (Junction to Case)

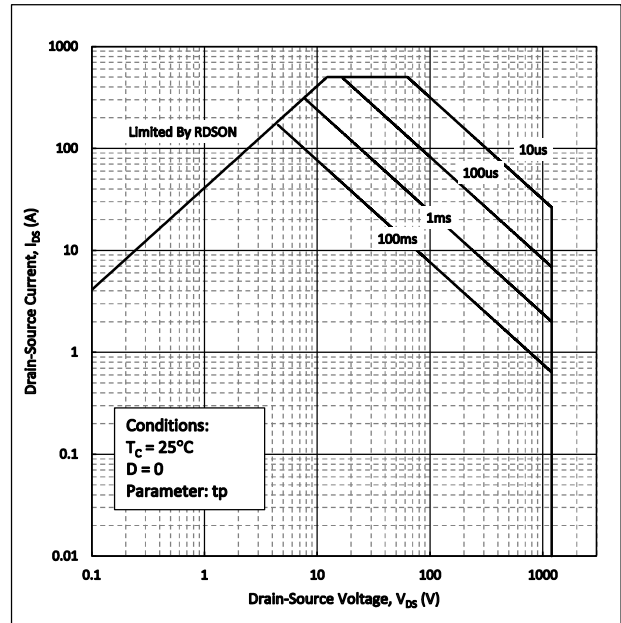


Figure 20. Safe Operating Area

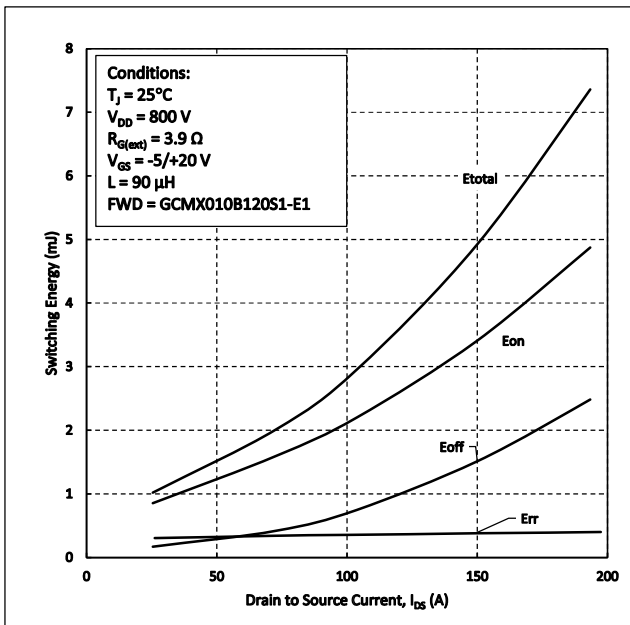


Figure 21. Clamped Inductive Switching Energy vs. Drain Current

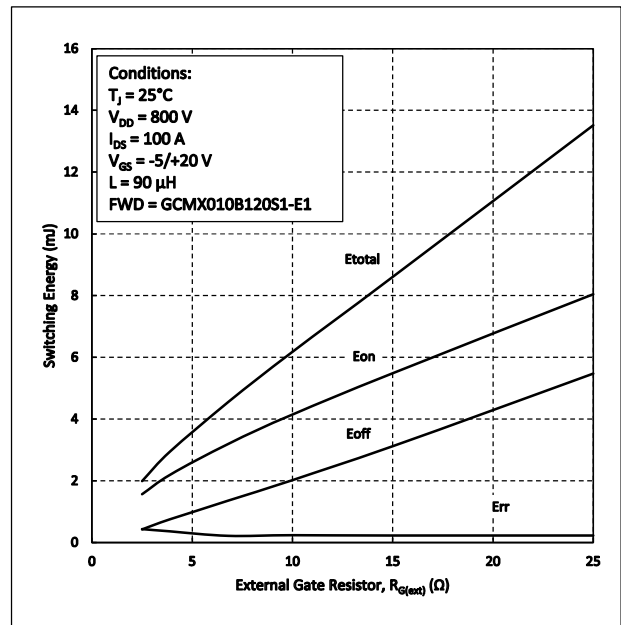


Figure 22. Clamped Inductive Switching Energy vs.  $R_{G(ext)}$



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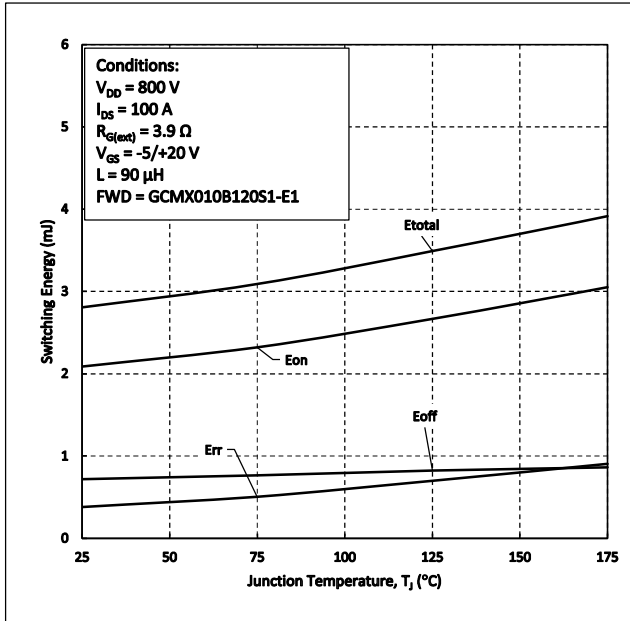


Figure 23. Clamped Inductive Switching Energy vs. Temperature

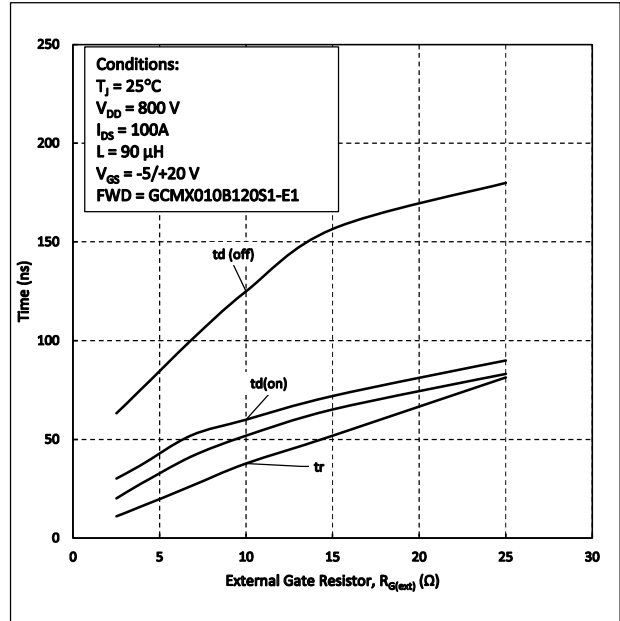


Figure 24. Switching Times vs  $R_{G(ext)}$

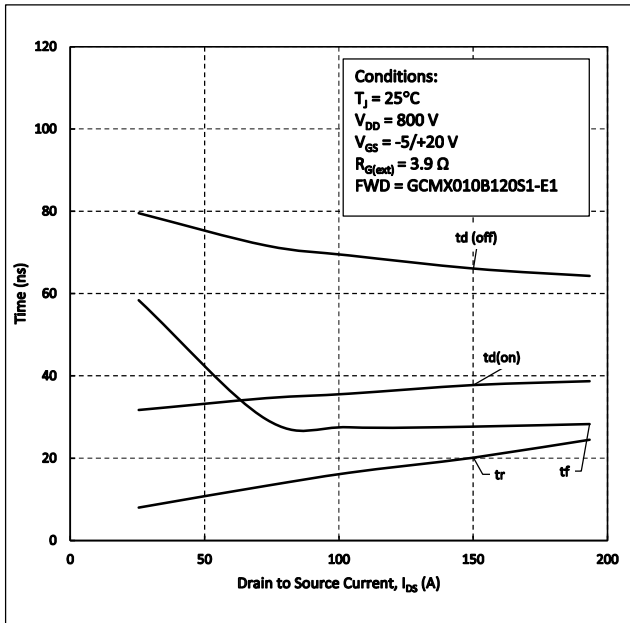


Figure 23. Switching Times vs. Drain Current

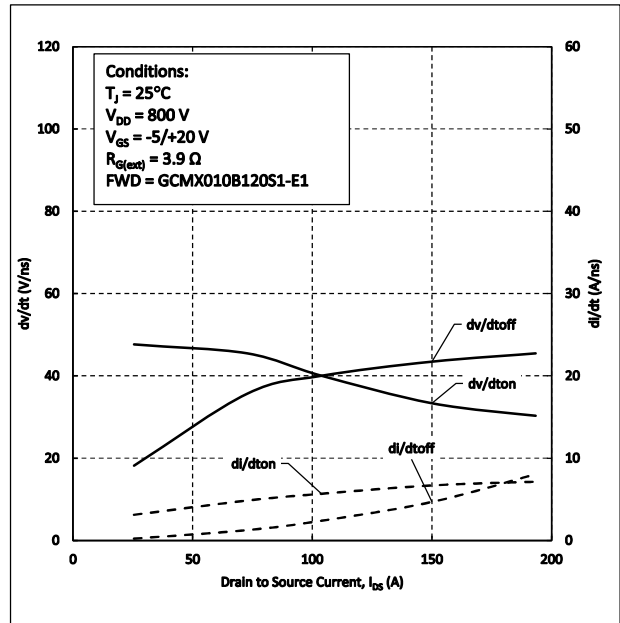


Figure 24.  $dv/dt$  and  $di/dt$  vs. Drain Current

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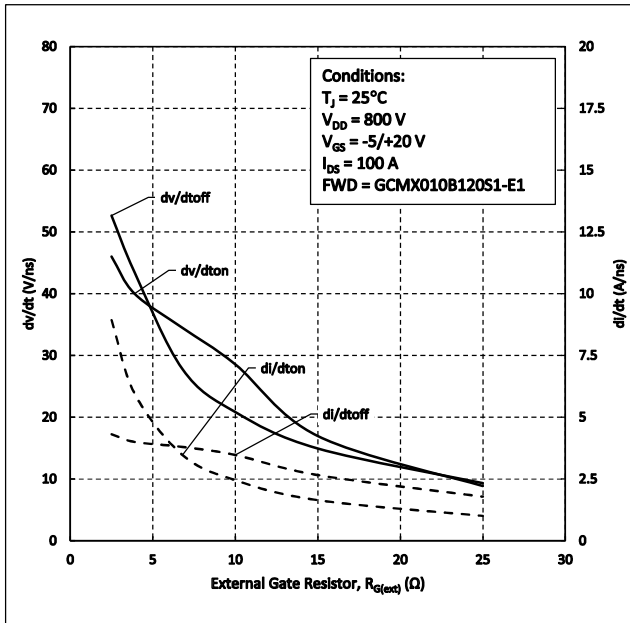


Figure 25.  $dv/dt$  and  $di/dt$  vs.  $R_{G(ext)}$

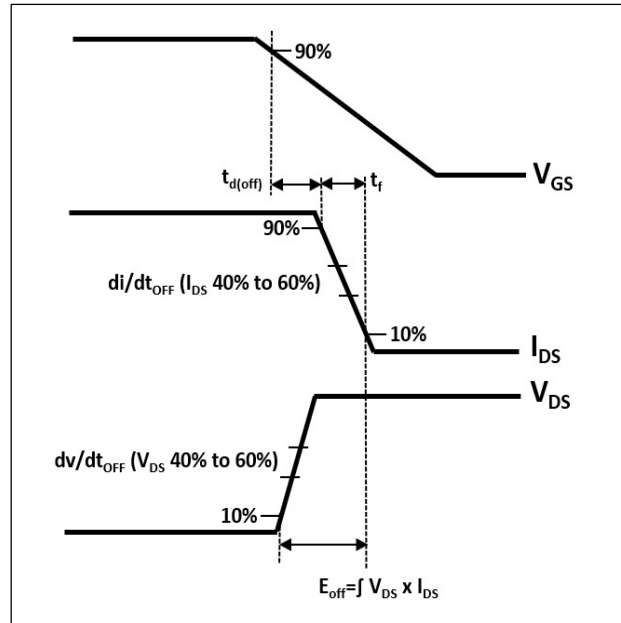


Figure 26. Turn-off Transient Definitions

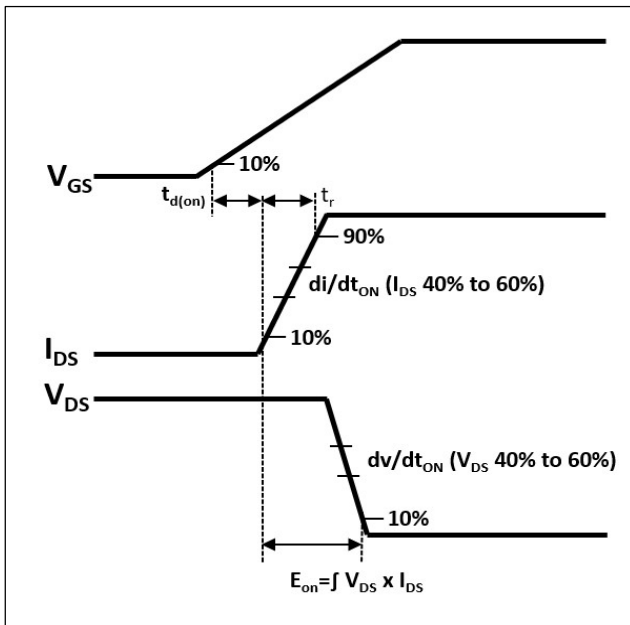


Figure 27. Turn-on Transient Definitions

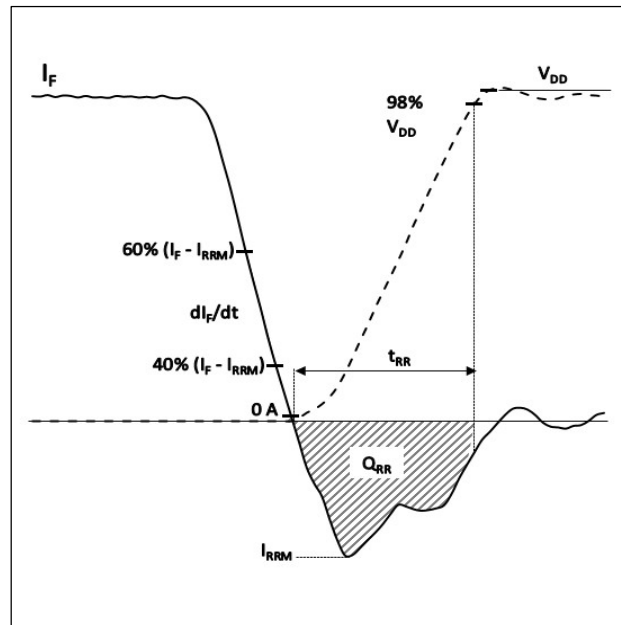
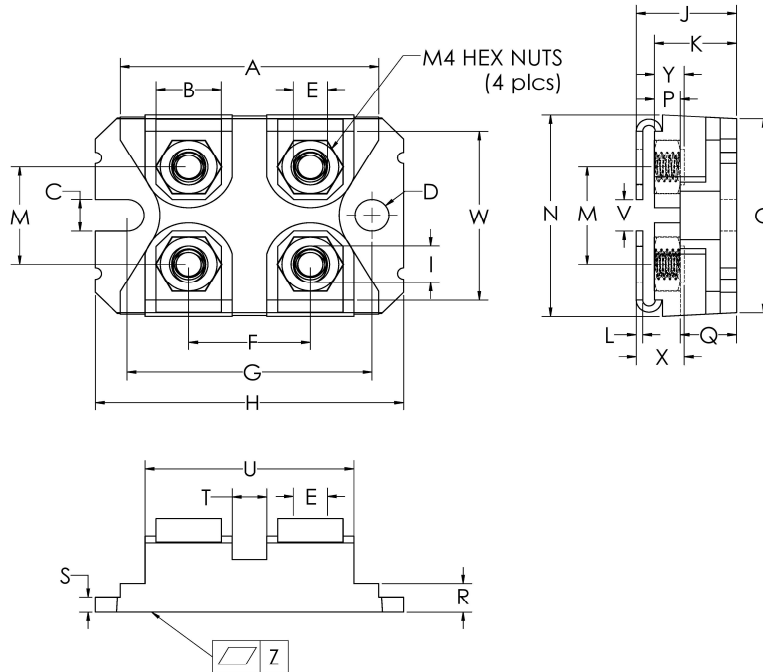


Figure 28. Reverse Recovery Definitions

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## Package Dimensions SOT-227



Sym	Millimeters		Inches	
	Min	Max	Min	Max
A	31.67	31.90	1.247	1.256
B	7.95	8.18	0.313	0.322
C	4.14	4.24	0.163	0.167
D	4.14	4.24	0.163	0.167
E	4.14	4.24	0.163	0.167
F	14.94	15.09	0.588	0.594
G	30.15	30.25	1.187	1.191
H	38.00	38.10	1.496	1.500
I	4.75	4.83	0.187	0.190
J	11.68	12.19	0.460	0.480
K	9.45	9.60	0.372	0.378
L	0.76	0.84	0.030	0.033
M	12.62	12.88	0.497	0.507
N	25.15	25.30	0.990	0.996
O	24.79	25.04	0.976	0.986
P	3.02	3.15	0.119	0.124
Q	6.71	6.96	0.264	0.274
R	4.17	4.42	0.164	0.174
S	2.08	2.13	0.082	0.084
T	3.28	3.63	0.129	0.143
U	26.75	26.90	1.053	1.059
V	3.86	4.24	0.152	0.167
W	20.55	26.90	0.809	0.814
X	5.45	5.85	0.215	0.230
Y	3.15	3.66	0.124	0.144
Z	0.00	0.13	0.000	0.005

Revision History		
Date	Revision	Notes
3/28/2023	0.1	Preliminary release

## Notes

### **RoHS Compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of [www.SemiQ.com](http://www.SemiQ.com).

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REACH substances of high concern (SVHC) information is available for this product. Since the European Chemicals Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact our office at SemiQ Headquarters in Lake Forest, California to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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